

00862.102568.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
KAZUYA NOTSU, ET AL.) Examiner: Not Yet Assigned
Application No.: U.S. National Stage of) Group Art Unit: Not Yet Assigned
PCT/JP2004/018982,)
filed December 14, 1004)
Filed: Not Yet Assigned)
For: SEMICONDUCTOR MEMBER,)
MANUFACTURING METHOD)
THEREOF, AND SEMICONDUCTOR)
DEVICE) June 22, 2005

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents are also enclosed.

For a concise explanation of relevance of the non-English documents, the Examiner is referred to the enclosed English-language abstracts, and to pages 2 and 13 of the specification.

Some of the listed documents were cited in a PCT International Search report mailed February 8, 2005 for International Application No. PCT/JP2004/018982, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

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JC17 Rec'd PCT/PTO 23 JUN 2005

Some of the listed documents were cited in a PCT International Search Report mailed March 29, 2005 for International Application No. PCT/JP2004/018981, which is the parent of the present application from which this application claims priority. A copy of this search report is also enclosed.

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,



John A. Krause
Attorney for Applicants
Registration No.: 24,613

FITZPATRICK, CELLA, HARPER & SCINTO
30 Rockefeller Plaza
New York, New York 10112-3800
Facsimile: (212) 218-2200

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FORM PTO 1449 (modified)			ATTY DOCKET NO.	APPLICATION NO.			
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			00862.102568.	10/15/0261 U.S. National Stage of PCT/JP2004/018982; filed December 14, 2004			
LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)			APPLICANT	KAZUYA NOTSU, ET AL.			
			FILING DATE	Not Yet Assigned	GROUP	Not Yet Assigned	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,221,413	06/22/93	Brasen et al.	117	89	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
		EP 1 248 294 A2	10/09/02	EPO			
		JP 2003-178977 A	06/27/03	Japan			Abstract
		JP 2003-282464 A	10/03/03	Japan			Abstract
		JP 2003-282463 A	10/03/03	Japan			Abstract
		JP 2004-342975 A	12/02/04	Japan			Abstract
		JP 2003-78118 A	03/14/03	Japan			Abstract
		JP 2003-78140	03/14/03	Japan			Abstract
		JP 11-195562	07/21/99	Japan			Abstract
		JP 7-302889	11/14/95	Japan			Abstract
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		Michael I. Current, et al. "Atomic-layer Cleaving with SiGe Strain Layers for Fabrication on Si and Ge-rich SOI Device Layers", IEEE International SOI Conference, October 2001, pp. 11-12.					
		Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.					
		T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).					
		D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).					
		D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).					
		A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).					
EXAMINER			DATE CONSIDERED				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1